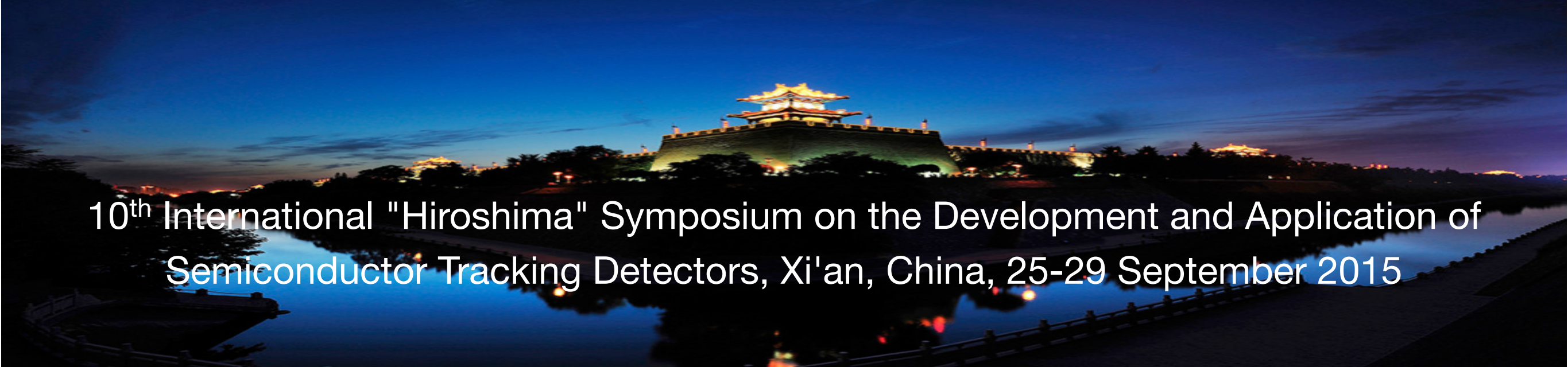


# Vertex Detector for the CEPC

## — A Prospective Overview

Hongbo Zhu (IHEP, Beijing)



10<sup>th</sup> International "Hiroshima" Symposium on the Development and Application of Semiconductor Tracking Detectors, Xi'an, China, 25-29 September 2015

# Outline

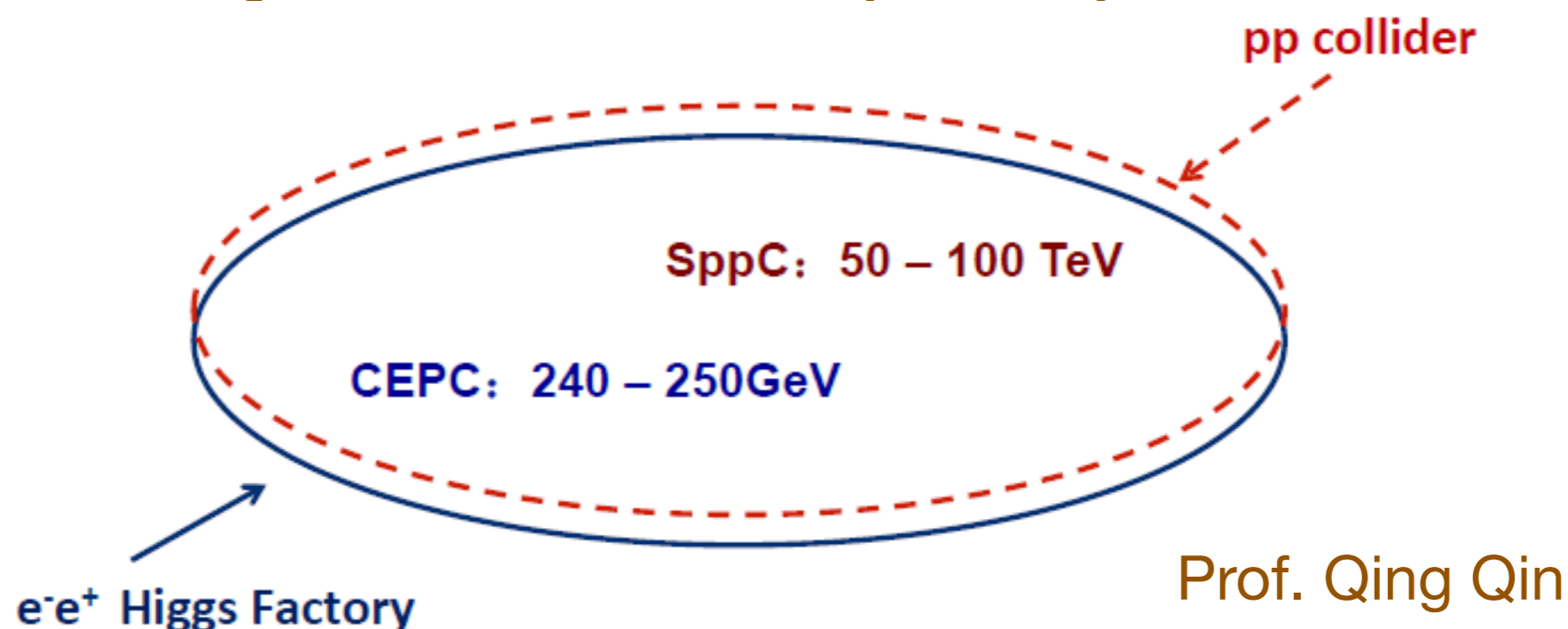
- Introduction to CEPC
- Performance requirements
- Candidate technologies
- R&D status
- Summary

# Introduction

- The **Higgs Discovery** in 2012 witnessed the breakthrough in the history of particle physics and triggered wave of thoughts on **Higgs Factories** around the world ...

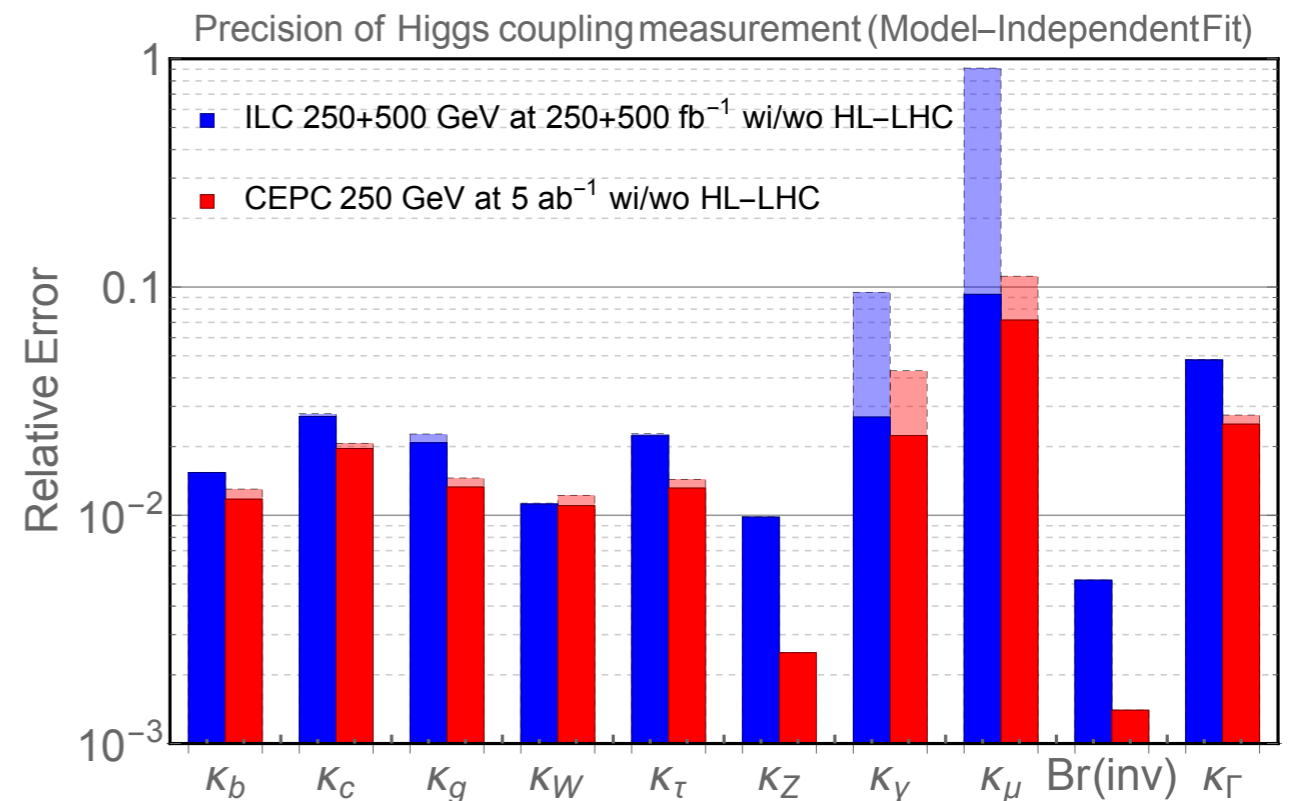
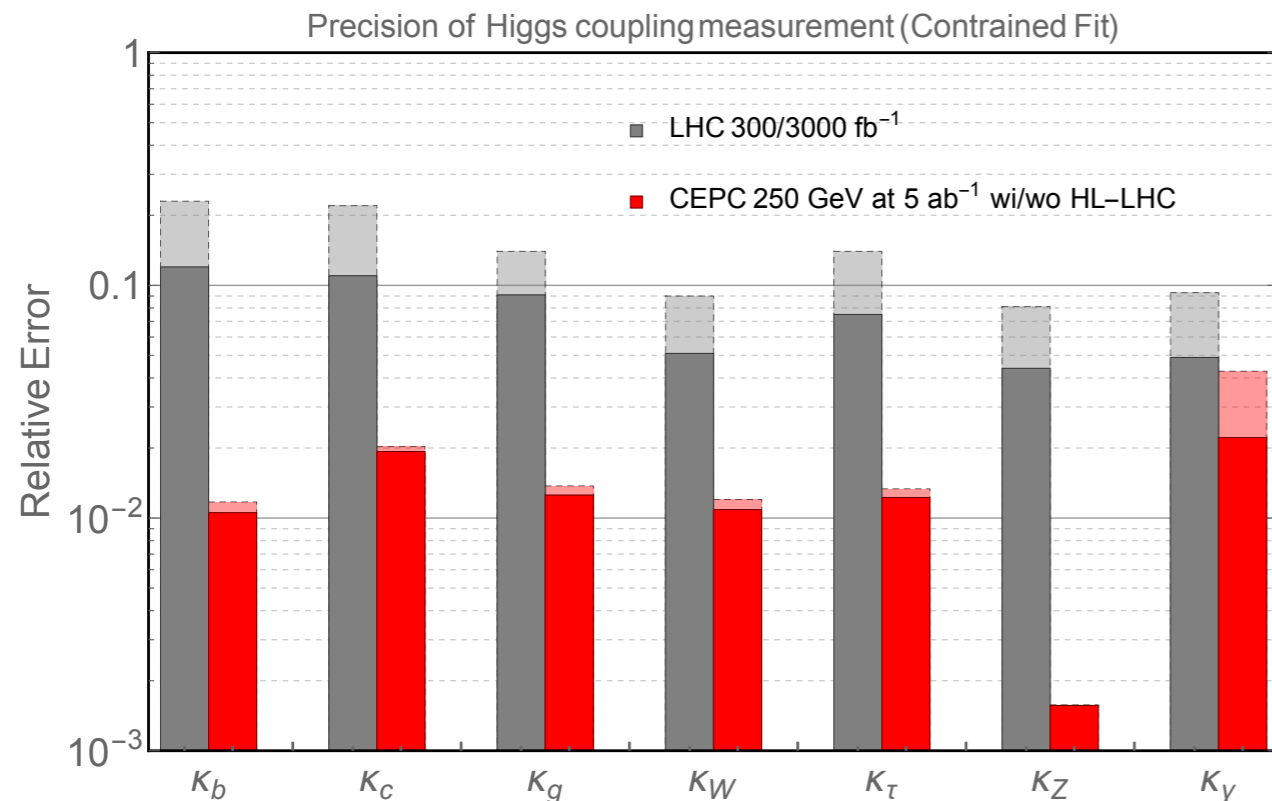
A. Bondel and F. Zimmerman, *A High Luminosity  $e^+e^-$  Collider in the LHC tunnel to study the Higgs Boson*, [arXiv:1112.2518](https://arxiv.org/abs/1112.2518), **even before the Higgs discovery!**

- Where the story began ... presented by Prof. Qing Qin at the **Accelerators for a Higgs Factory: Linear vs. Circular (HF2012)**



# Circular Electron Positron Collider

- **Circular Electron Positron Collider (CEPC)** to collide electron/positron beams at  $\sqrt{s} \sim 240$  GeV with a peak luminosity of  $2 \times 10^{34} \text{ cm}^{-2}\text{s}^{-1}$ , and 2 IP to deliver  $\sim 1\text{M}$  clean ZH events over 10 years  $\rightarrow$  **Higgs Factory**
  - *Higgs mass, cross section, branching ratios, couplings etc.*
- Operate at Z-pole/WW threshold  $\rightarrow$  **EW precision measurements**

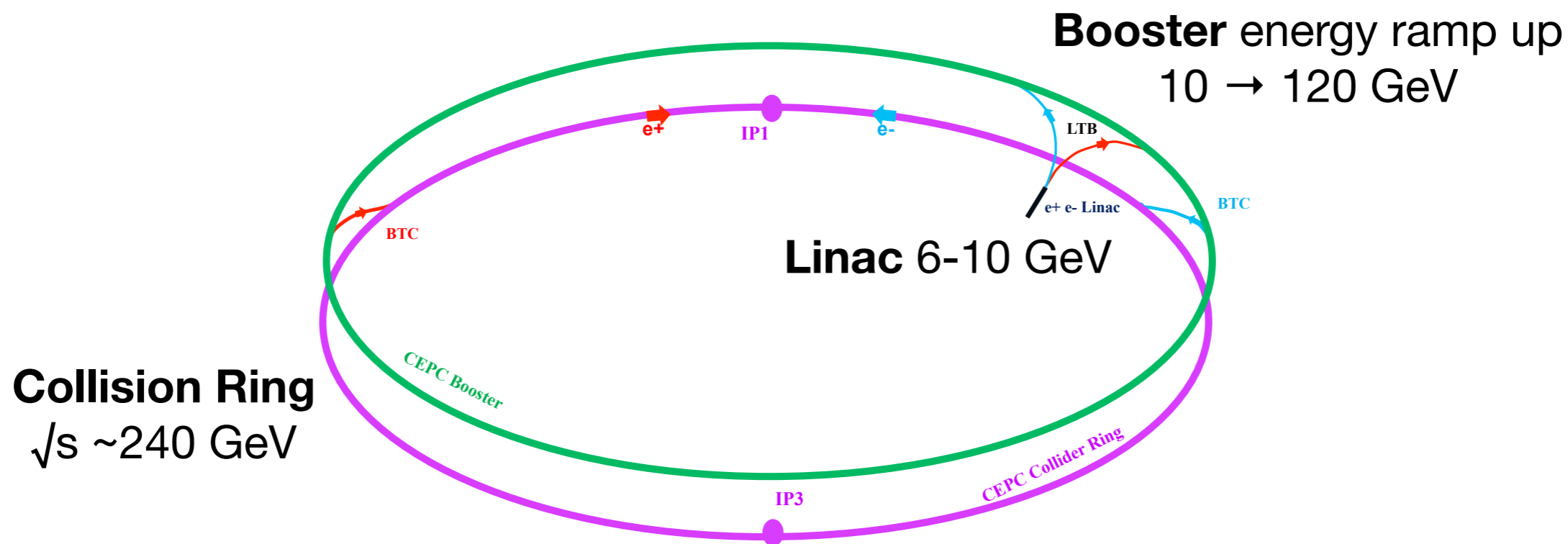


# Possible Project Timeline

## CEPC



**1<sup>st</sup> Milestone:** pre-CDR (by the end of 2014) → R&D funding request to Chinese government in 2015 (China's 13<sup>th</sup> Five-Year Plan 2016-2020)

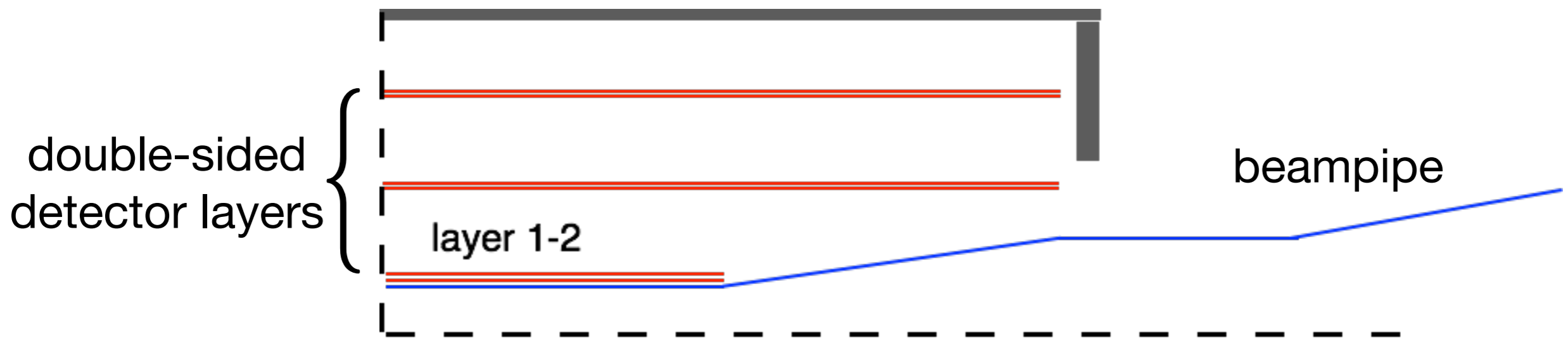


# Vertex Detector

- Crucial to achieve high impact parameter resolution, which is required for heavy flavour (b/c) and  $\tau$ -tagging:

$$\sigma_{r\phi} = 5 \oplus 10/p \cdot \sin^{3/2} \theta \text{ } \mu\text{m}$$

- For the physics feasibility studies, the ILD vertex detector layout has been adopted, which features 3 double-sided layers ranging between 1.6 -6.0 cm



# Performance Requirements

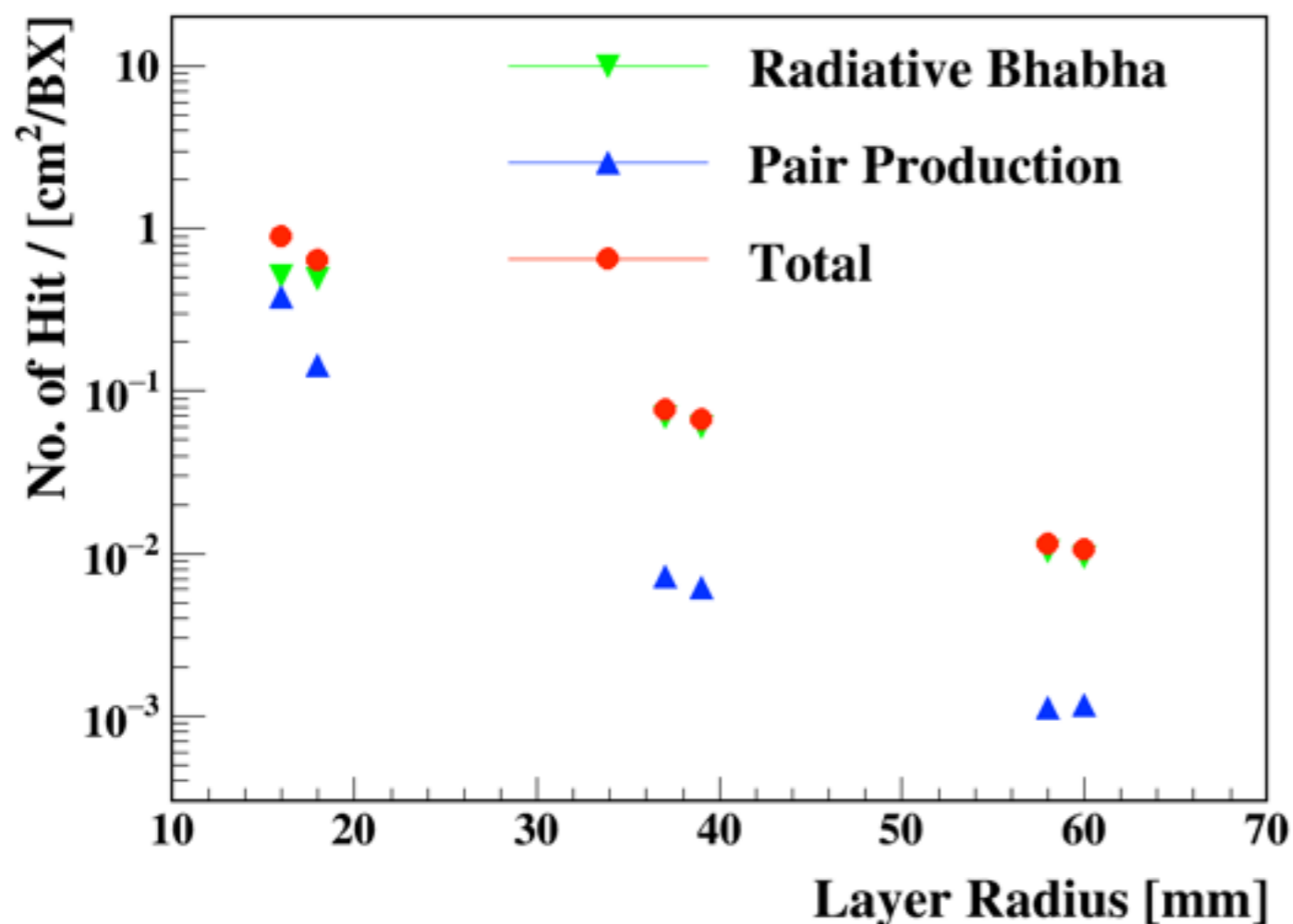
$$\sigma_{r\phi} = 5 \oplus 10/p \cdot \sin^{3/2} \theta \text{ } \mu\text{m}$$

- Imposing stringent requirements on the Vertex detector
  - ▶ **Spatial resolution near the interaction point  $\sigma_{SP} \leq 3 \text{ } \mu\text{m}$**  → high granularity (small pixel size)
  - ▶ **Material budget  $\leq 0.15\% X_0/\text{layer}$**  → monolithic pixel sensor (sensor + embedded electronics, thinned down to e.g.  $50 \text{ } \mu\text{m}$ ) + air cooling (power dissipation  $\leq 50 \text{ mW/cm}^2$ )
  - ▶ **Low detector occupancy below 0.5%** → high granularity and short integration time
  - ▶ **Radiation tolerance (pre.):**  $\sim 1 \text{ MRad}$  (TID) and  $10^{12} \text{ n}_{\text{eq}}/\text{cm}^2$  (NIEL)

Similar to the ILC vertex detector requirements but **without power-pulsing**

# Hit Density

- Critical parameter to determine the segmentation (+ physics requirements) and readout time of pixel sensors
- Mostly driven by background events originating from pair production, radiative Bhabha scattering, synchrotron radiation ...



bunch spacing  $\sim 3.6 \mu\text{s}$

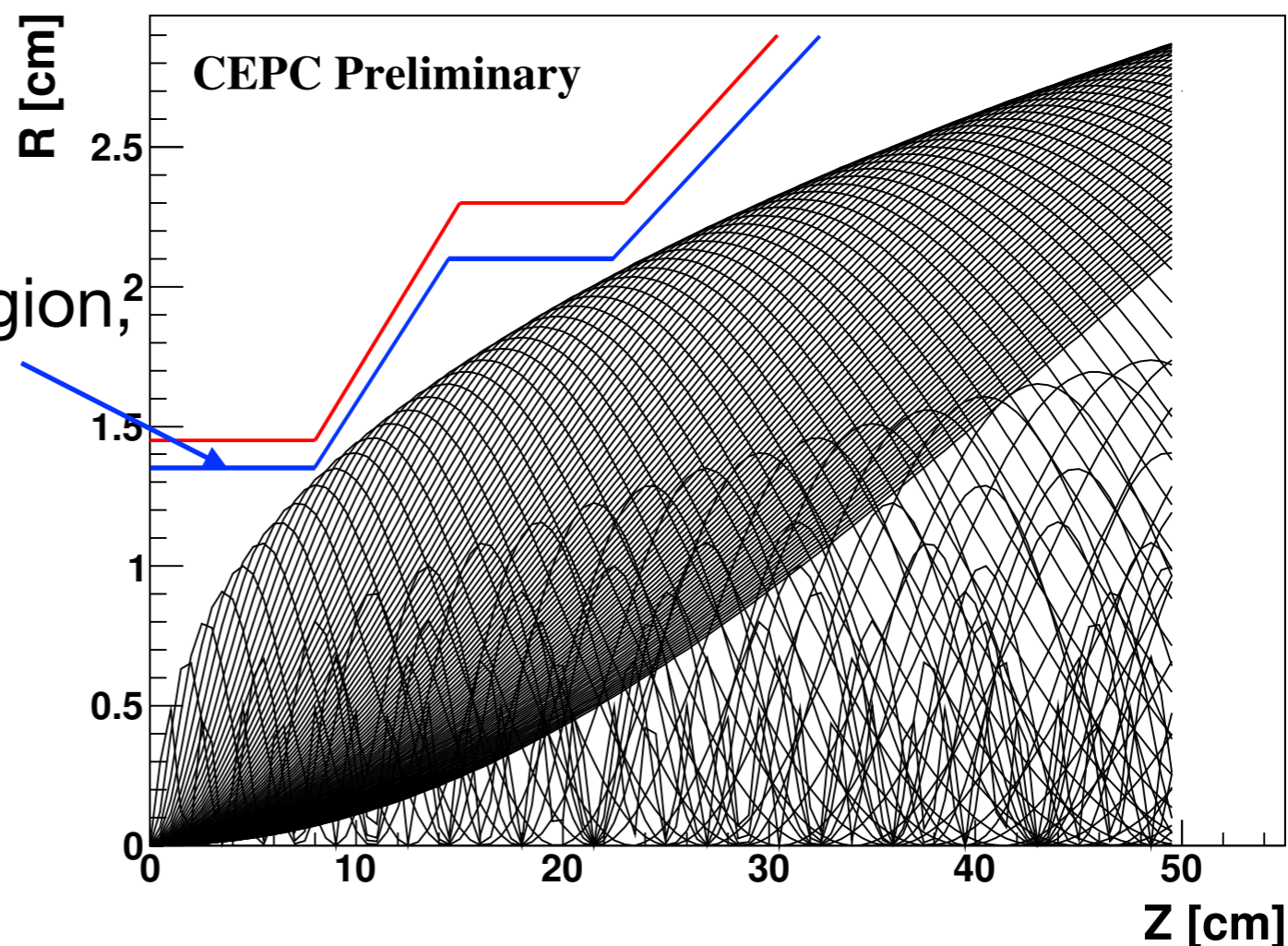


# Layout Optimisation

- The 1st vertex detector layer as close as possible to IP to minimise the extrapolation uncertainty and to improve the impact parameter resolution
- Electrons/positrons from pair production will develop a “kinematic edge” and detector components and beampipe should be kept sufficiently far away from this edge.

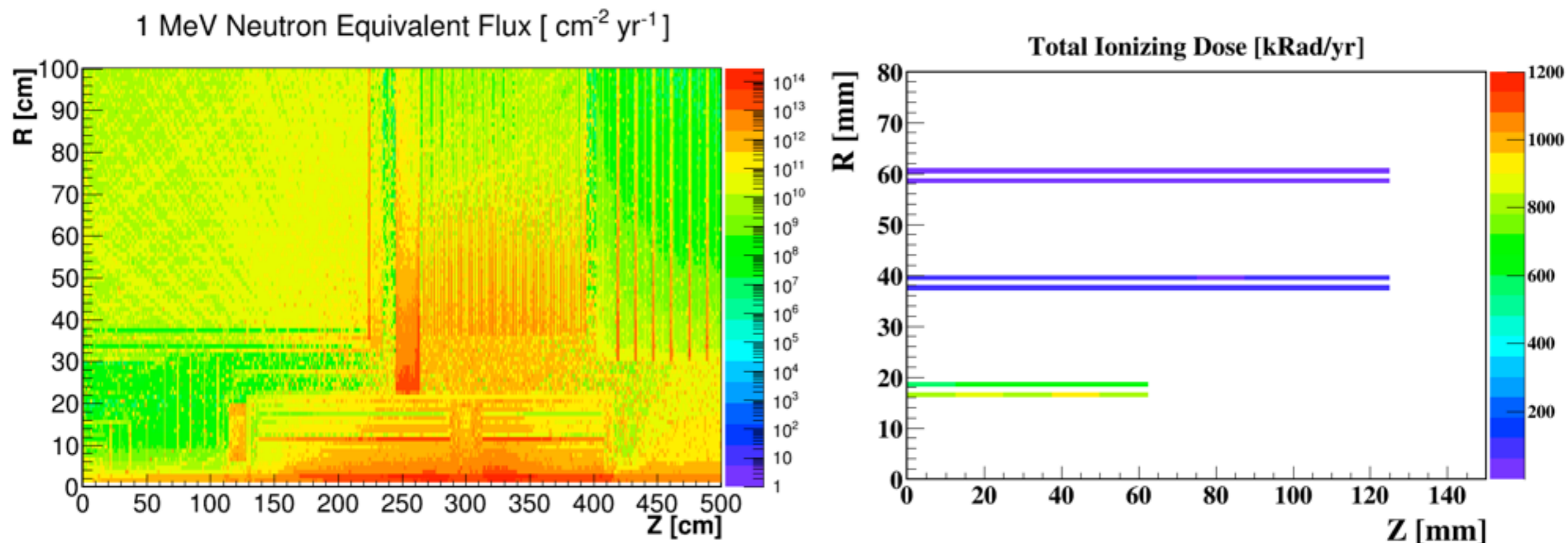
possible to push the beampipe closer by **1 mm** in the central region,<sup>2</sup> and exact gain to be estimated

general strategy for layout optimisation being developed



# Radiation Levels

- Benign radiation environment by the (HL-)LHC standard, but still considerable



Annual values (including safety factors of 5):

**NIEL:  $10^{12} \text{ n}_{\text{eq}}/\text{cm}^2$**  and **TID: 1 MRad**

# Candidate Technologies

- Monolithic pixel sensor technologies considered:
  - ▶ **CMOS**: Ultimate installed for STAR PXL, technology for ALICE ITS upgrade, pursued by ATLAS for Pixel Phase-II upgrade ...
  - ▶ **DEPFET**: Belle-II pixel detector (attractive feature of self-supporting structure with low material budget in the active volume)
  - ▶ **SOI**: actively pursued for X-ray detection (existing design expertise, see Yunpeng Lu's talk), potential issue with radiation tolerance
  - ▶ **3D-IC**: trials within the 3D consortium, promising (ultimate detector) but technology not mature enough
- Given the technology maturity and accessibility, **CMOS technology (TJ CIS 0.18  $\mu\text{m}$ )** has been chosen for initial sensor R&D.

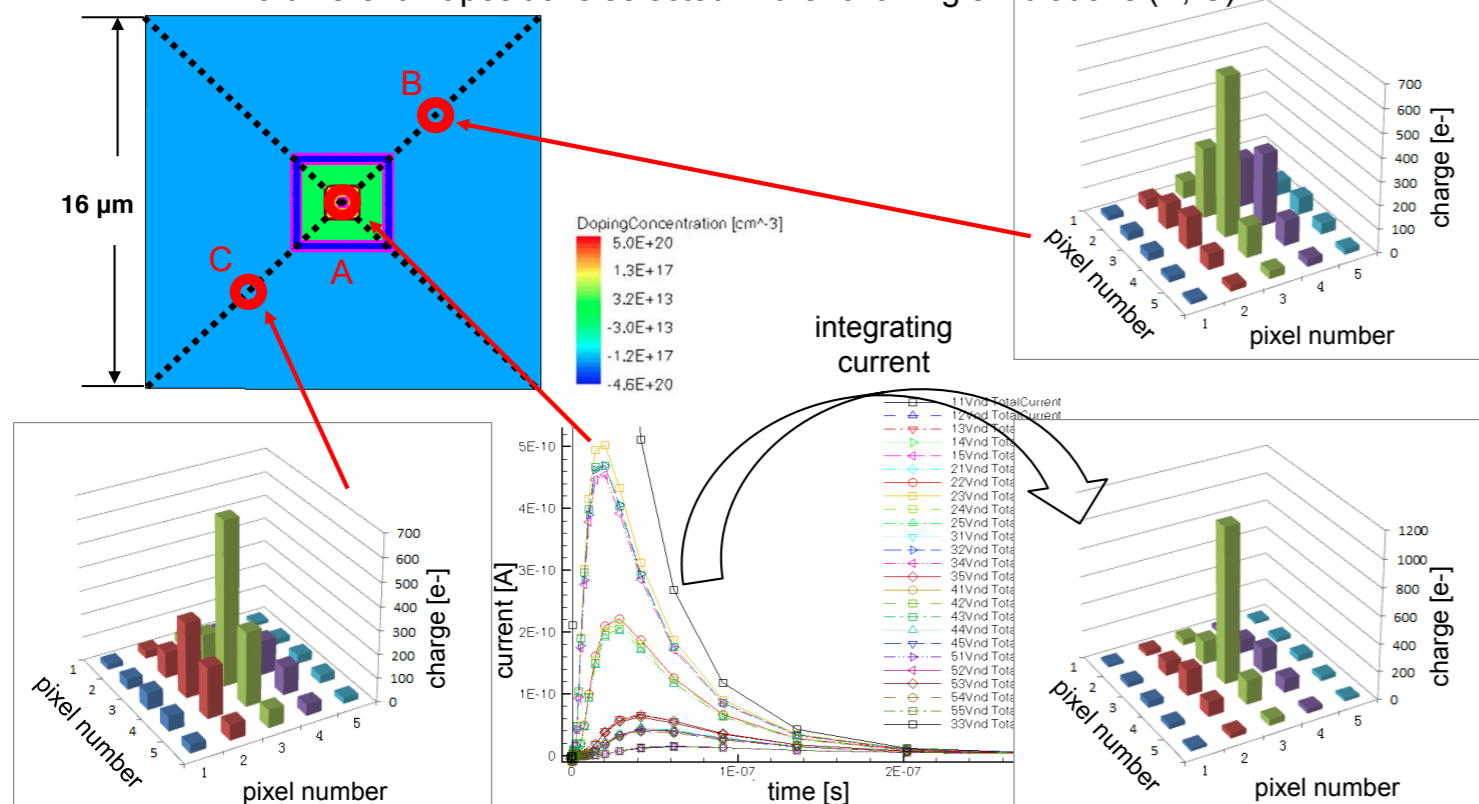
# Early Stage R&D

- Important to understand the charge collection efficiency with different diode geometries, epitaxial layer resistivity and thickness, radiation damage ... , TCAD simulation followed by measurements → **sensor optimisation**

## Charge collection vs. hit position

- The symmetrical pixel model makes the charge collection distribution symmetrical

Two different hit positions selected in the following simulations (A, C)



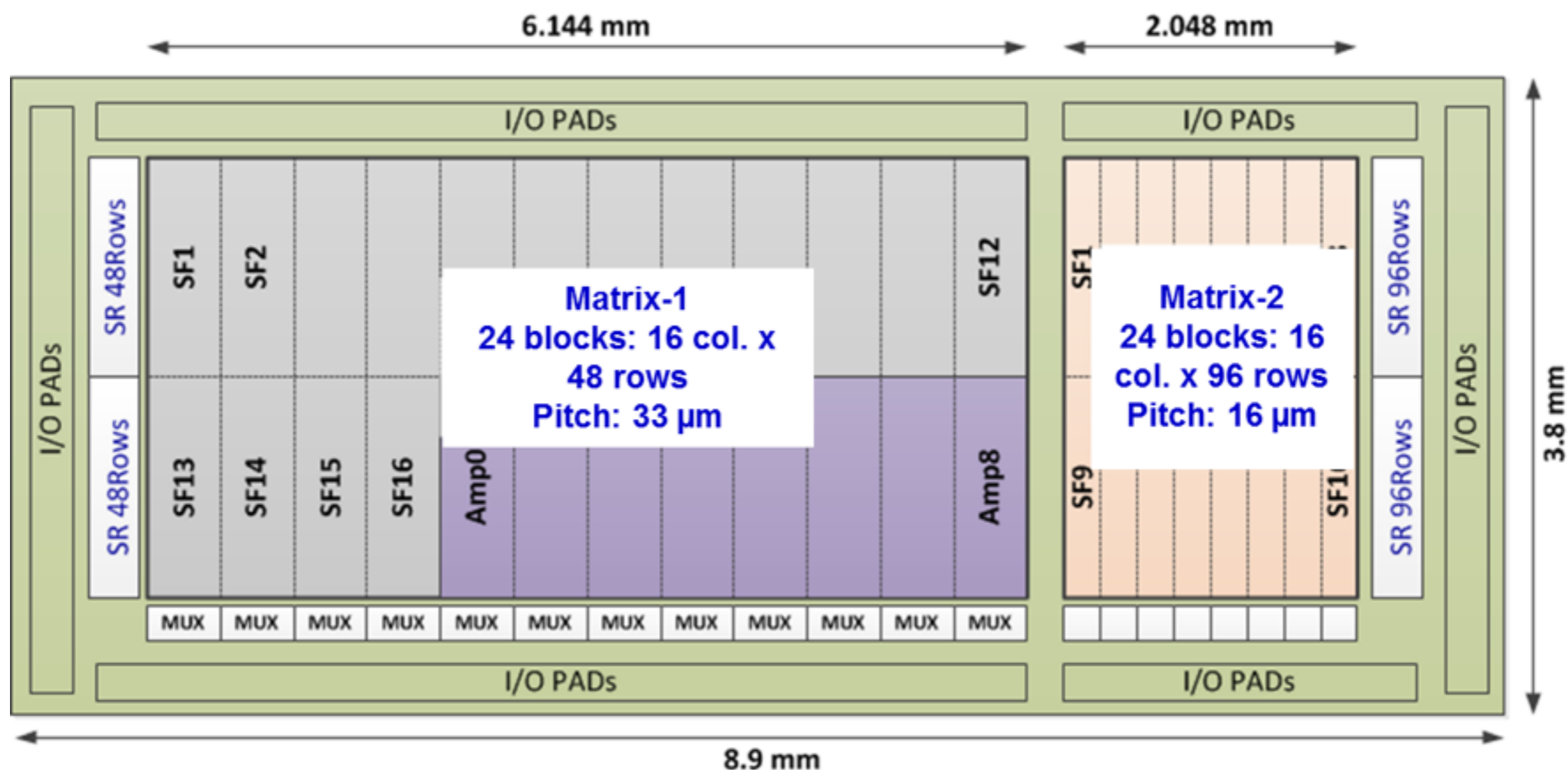
Sector	Diode area	Footprint	Structure
SFB1	3 μm <sup>2</sup>	20 μm <sup>2</sup>	2T_nmos
SFB2	4 μm <sup>2</sup>	20 μm <sup>2</sup>	2T_nmos
SFB3	8 μm <sup>2</sup>	20 μm <sup>2</sup>	2T_nmos
SFB4	3 μm <sup>2</sup>	15 μm <sup>2</sup>	2T_nmos
SFB5	4 μm <sup>2</sup>	15 μm <sup>2</sup>	2T_nmos
SFB6	8 μm <sup>2</sup>	15 μm <sup>2</sup>	2T_nmos
SFB7	3 μm <sup>2</sup>	11 μm <sup>2</sup>	2T_nmos
SFB8	4 μm <sup>2</sup>	11 μm <sup>2</sup>	2T_nmos
SFB9	8 μm <sup>2</sup>	11 μm <sup>2</sup>	2T_nmos
SFB10	3 μm <sup>2</sup>	8 μm <sup>2</sup>	2T_nmos
SFB11	4 μm <sup>2</sup>	8 μm <sup>2</sup>	2T_nmos
SFB12	8 μm <sup>2</sup>	8 μm <sup>2</sup>	2T_nmos
SFB13	8 μm <sup>2</sup>	20 μm <sup>2</sup>	2T_pmos
SFB14	4 μm <sup>2</sup>	8 μm <sup>2</sup>	2T_pmos
SFB15	8 μm <sup>2</sup>	20 μm <sup>2</sup>	3T_nmos
SFB16	4 μm <sup>2</sup>	8 μm <sup>2</sup>	3T_nmos

See Ying Zhang's talk



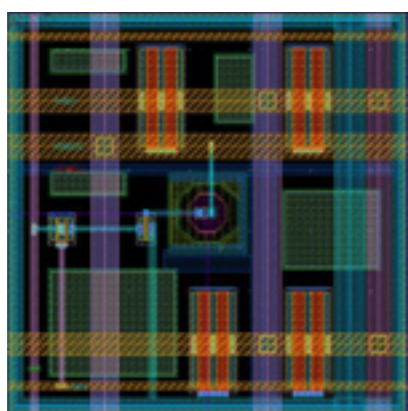
# First Submission

- Submission mainly for charge collection optimisation, but with several blocks reserved for analog circuit studies (e.g. amplifiers)



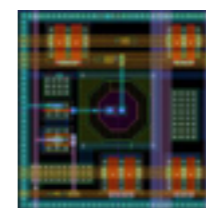
# Considerations

- **Pixel sizes** of  $16 \times 16 \mu\text{m}^2$  (binary readout) and  $33 \times 33 \mu\text{m}^2$  (multi-bit ADC) to achieve  $3\mu\text{m}$  resolution with constraints: 1. power consumption, 2.) effective area  $\rightarrow$  possible alleviation with **extension in z** (z resolution loss to be studied with physics simulation) or **3D-IC** (analog/digital tiers)



$33 \times 33 \mu\text{m}^2$

areas filled up with capacitors  
possible for implanting more  
transistors



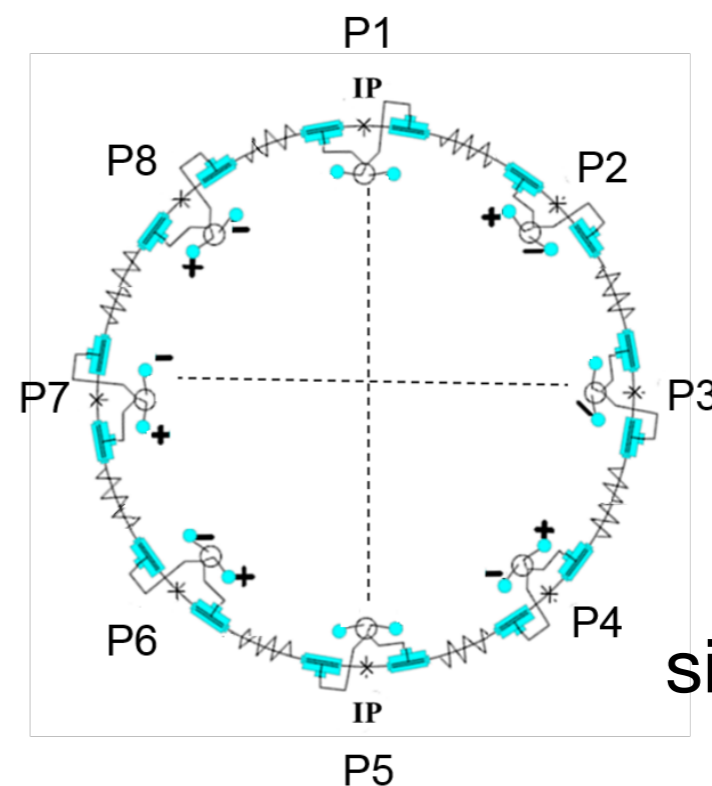
completely filled up

$16 \times 16 \mu\text{m}^2$

- **Readout architecture:** digitisation in pixel (to minimise power dissipation to drive analog signal) and sparsified readout  $\rightarrow$  e.g. ALPIDE for the ALICE ITS
- **Cooling technique:** force-air cooling demonstrated for STAR PXL and thermal simulation for CLIC vertex detector, or more aggressive with micro channel cooling (LHCb)

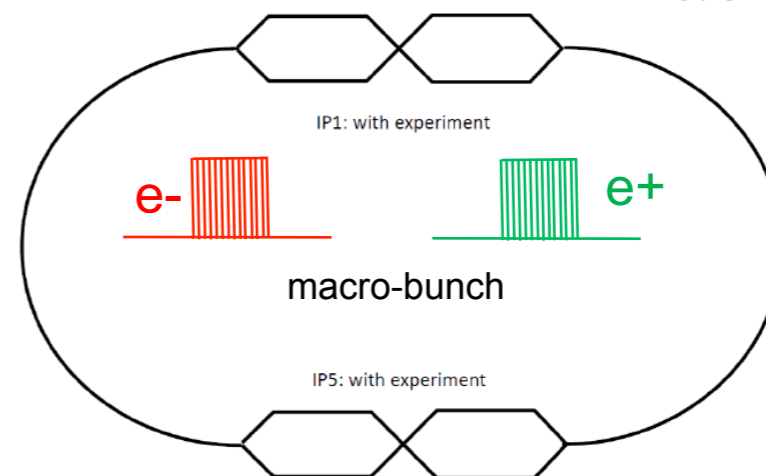
# Moving Target

- As the accelerator design evolves, the requirements on the vertex detector might have to change.
- Increased backgrounds would lead to in higher radiation tolerance requirement and time-stamping capability ( $O(10\text{ns})$ ) to distinguish bunch crossings.
- Necessary to revise the sensor specifications and readout requirements in near future.



single bunch

macro-bunch train



# Summary

- Circular Electron Positron Collider (CEPC) as a Higgs Factory → **precision Higgs measurements**
- Performance requirements on the vertex detector similar to that of the ILD but with special considerations on power consumption and backgrounds → **might have to be revised**
- Pixel sensor R&D based on CMOS technology has just started with sensor charge collection optimisation

**Thank you for your attention!**



# Luminosity

